Beceipt date: 04/02/2010

10791334 - GALL: 1715

Doc description: Information Disclosure Statement (IDS) Filed

Approved for use through 07/31/2012. OMB 0651-0031
U.S. Patent and Trademark Office; U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Not for submission under 37 CFR 1.99)

Application Number		10791334			
Filing Date		2004-03-01			
First Named Inventor	Gi Yo	ul Kim			
Art Unit		1792			
Examiner Name	David	P. Turocy			
Attorney Docket Number		40004551-0025-002			

				U.S.	PATENTS	Remove			
Examiner Initial*	Cite No			Issue Date	Name of Patentee or Applicant of cited Document	Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear			
	1	4389973		1983-06-28	Suntola, T.S. et al.				
	2	5281274		1994-01-25	Yoder, Max N.				
	3	5855675		1997-03-03	Doering, Kenneth et al.				
	4	5879459		1999-03-09	Gadgil, Prasad N. et al.				
	5	6042652		2000-03-28	Hyun, Kwang-soo et al.				
	6	6174377		2001-01-16	Doering, Kenneth et al.				
	7	6387185		2002-05-14	Doering, Kenneth et al.				
	8	6503330		2003-01-07	Sneh, Ofer et al.				

Receipt date: 04/02/2010 INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)					Application Number				10791334	107	91334 -	GAU: 1	715
					Filing	Date			2004-03-01				
					First Named Inventor Gi You			ul Kim					
					Art Unit				1792				
					Examiner Name David				P. Turocy				
					Attorney Docket Number			er	40004551-0025-0	002			
				<u> </u>									
	9	6270572		2001-08-07		Kim, Yeong-kwan et		n et al.					
	10	6	306216		2001-10-23		Kim, Yong II et al.						
If you wish	n to ad	ld a	dditional U.S. Paten	ıt citatio	information please click the Ad				dd button.		Add		
,						ATENT APPLICATION PUBLICATIONS					Remove		
										D	0-1	:	_
Examiner Initial*			Publication Number	Kind Code ¹	Publica Date	tion	Name of Patent of cited Docume		• • •	Releva	s,Columns,l ant Passag es Appear		
	1	20050260348 2005-11-24 Lee, Jung-hyu		hyun e	et al.								
If you wish	n to ad	d a	dditional U.S. Publis	shed Ap	plication	citation	ı ı informatio	on ple	ase click the Add	d buttor	n. Add		
-				<u> </u>	FOREIC	N PAT	ENT DOC	UMEI	NTS		Remove		
Examiner Initial*	Cite No	Foreign Document Country Number ³ Code ² i					Publicatio Date	n A	Name of Patentee or Applicant of cited Document		Pages,Columns,Lines where Relevant Passages or Relevant Figures Appear		T5
	1												
If you wisl	n to ad	d a	dditional Foreign Pa	atent Do	cument	citation	informatio	n plea	ase click the Add	button	Add		
				NON	I-PATEN	IT LITE	RATURE	DOC	JMENTS		Remove		
Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue number(s), publisher, city and/or country where published.										T 5	
	1	S.M. GEORGE "Atomic Layer Deposition: An Overview", Chem. Rev., 110, pp. 111-131 (2010)											
	2	R.A. WIND and S.M. GEORGE "Quartz Crystal Microbalance Studies of Al2O3 Atomic Layer Deposition Using Trimethylaluminum and Water at 125°C", J. Phys. Chem. A, 114, pp. 1281-1289 (2010)											

Receipt date: 04/02/2010			Δ	Application Number	10791334	10	791334	- GAU:	1715			
INFORMATION DISCLOSURE					iling Date	10791334 10791334 - GAU: 1715 2004-03-01						
							oul Kim					
STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)				A	Art Unit		1792					
				E	Examiner Name David P. Turocy							
				A	Attorney Docket Num	40004551-0025-002						
		1347		D.	atan ill Occide C	h.4:1	-land for This Ti	l O				
	3	J.W. ELAM et al., "Viscous Flow Reactor with Quartz Crystal Microbalance for Thin Film Growth by Atomic Layer Deposition", Rev. Sci. Instrum., 73, pp. 2981-2987 (2002)										
	4	A.W. OTT et al., "Al2O3 Thin Film Growth on Si(100) Using Binary Reaction Sequence Chemistry", Thin Solid Films, 292, pp. 135-144 (1997)										
	5	M.D. GRONER et al., "Low Temperature Al2O3 Atomic Layer Deposition", Chem. Mater., 16, pp. 639-645 (2004)										
If you wis	h to ac	dd add	litional non-patent lite	ature o	document citation info	rmatio	n please click th	e Add	button A	d d		
					EXAMINER SIGNA	TURE						
Examiner Signature /David Turocy/							Date Consid	lered	05/12	/2010		
			reference considered, mance and not consider								a	
Standard S	T.3). ³ F	For Japa	O Patent Documents at www. anese patent documents, the appropriate symbols as indi	e indicat	tion of the year of the reign	of the E	mperor must preced	de the se	rial number o	of the patent o	document.	

English language translation is attached.